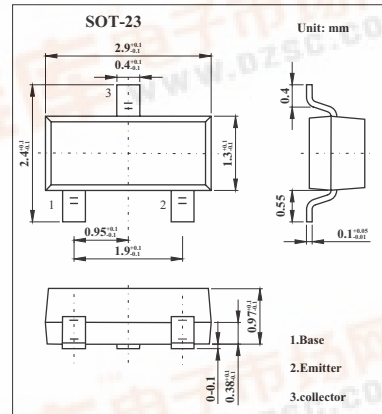


SMD Type Transistors

High Performance Transistor
FMMT451

■ Features

- Low equivalent on-resistance.
- 1 Amp continuous current.
- P_{tot} = 500mW.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	80	V
Collector-emitter voltage	V _{CEO}	60	V
Emitter-base voltage	V _{EB0}	5	V
Peak collector current	I _{CM}	2	A
Collector current	I _C	1	A
Base current	I _B	200	mA
Power dissipation	P _{tot}	500	mW
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA	80			V
Collector-emitter breakdown voltage *	V _{(BR)CEO}	I _C =10mA	60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA	5			V
Collector cutoff current	I _{CBO}	V _{CB} =60V			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V			0.1	μA
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C =150mA, I _B =15mA			0.35	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C =150mA, I _B =15mA			1.1	V
Static Forward Current Transfer Ratio *	h _{FE}	I _C =1A, V _{CE} =10V	10			
		I _C =150mA, V _{CE} =10V	50		150	
Current-gain-bandwidth product	f _T	I _C =50mA, V _{CE} =10V, f=100MHz	150			MHz
Output capacitance	C _{obo}	V _{CB} =10V, f=1MHz			15	pF

* Pulse test: t_p ≤ 300 μs; d ≤ 0.02.

■ Marking

Marking	451
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